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(54) **PROCESS FOR FABRICATING AN ISOLATED FIELD EFFECT TRANSISTOR IN AN EPI-LESS SUBSTRATE**

VERFAHREN ZUR HERSTELLUNG EINES ISOLIERTEN FELDEFFEKT-TRANSISTORS IN EINEM EPI-LOSEN SUBSTRAT

PROCEDE D'FABRICATION D'UN TRANSISTOR A EFFET DE CHAMP ISOLE DANS UN SUBSTRAT DEPOURVU DE COUCHE EPITAXIALE

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